

## 530N15N-VB TO262 Datasheet

### N-Channel 150-V (D-S) 175 °C MOSFET

#### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
150	0.030 at $V_{GS} = 10$ V	50
	0.033 at $V_{GS} = 6$ V	45

#### FEATURES

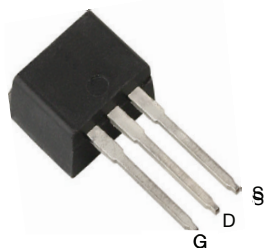
- Trench Power MOSFETs
- 175 °C Junction Temperature
- New Low Thermal Resistance Package
- PWM Optimized
- Compliant to RoHS Directive 2002/95/EC


**RoHS**  
 COMPLIANT

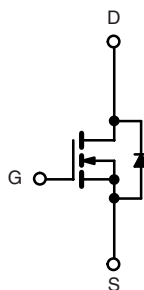
#### APPLICATIONS

- Primary Side Switch

TO-262



Top View



N-Channel MOSFET

#### ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	150	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 175$ °C)	$I_D$	50	A
		35	
Pulsed Drain Current	$I_{DM}$	150	
Avalanche Current	$I_{AR}$	50	
Repetitive Avalanche Energy <sup>a</sup>	$E_{AR}$	80	mJ
Maximum Power Dissipation <sup>a</sup>	$P_D$	166 <sup>b</sup>	W
		3.75	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 175	°C

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount TO-263 <sup>c</sup> )	$R_{thJA}$	40	°C/W
Junction-to-Case (Drain)	$R_{thJC}$	0.9	

Notes:

a. Duty cycle  $\leq 1$  %.

b. See SOA curve for voltage derating.

c. When Mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>DS</sub> = 0 V, I <sub>D</sub> = 250 μA	150			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2		4	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	
		V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	80			A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A		0.030		Ω
		V <sub>GS</sub> = 6 V, I <sub>D</sub> = 10 A		0.033		
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C		0.076		
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C		0.100		
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A	10			S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		2500		pF
Output Capacitance	C <sub>oss</sub>			290		
Reverse Transfer Capacitance	C <sub>rss</sub>			190		
Gate Resistance	R <sub>g</sub>			2		Ω
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 40 A		38	60	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			13		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			13		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 75 V, R <sub>L</sub> = 1.80 Ω I <sub>D</sub> ≅ 40 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 2.5 Ω		15	25	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			130	200	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			30	45	
Fall Time <sup>c</sup>	t <sub>f</sub>			90	140	
Source-Drain Diode Ratings and Characteristics T <sub>C</sub> = 25 °C <sup>b</sup>						
Continuous Current	I <sub>S</sub>				40	A
Pulsed Current	I <sub>SM</sub>				80	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 40 A, V <sub>GS</sub> = 0 V		1.0	1.5	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 40 A, dI/dt = 100 A/μs		100	150	ns
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>			5	8	A
Reverse Recovery Charge	Q <sub>rr</sub>				0.25	0.6

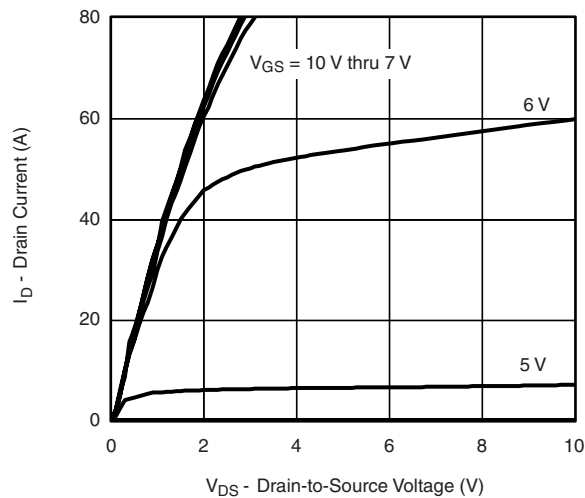
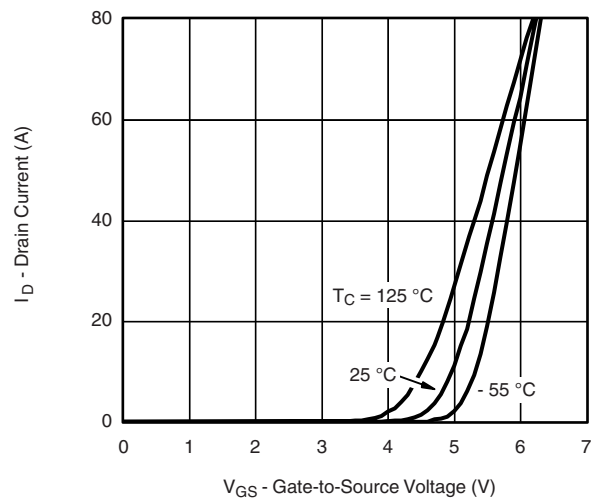
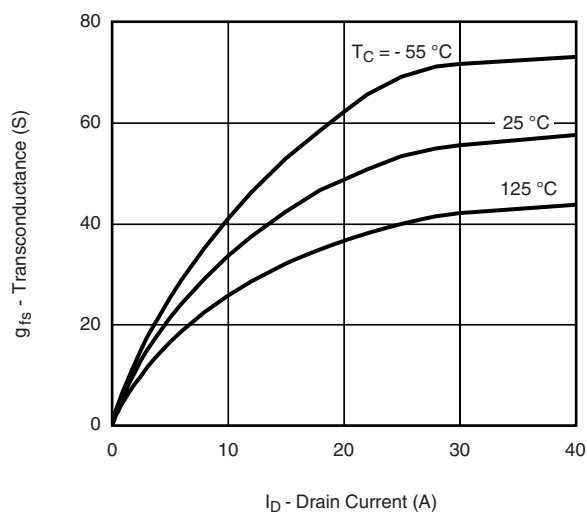
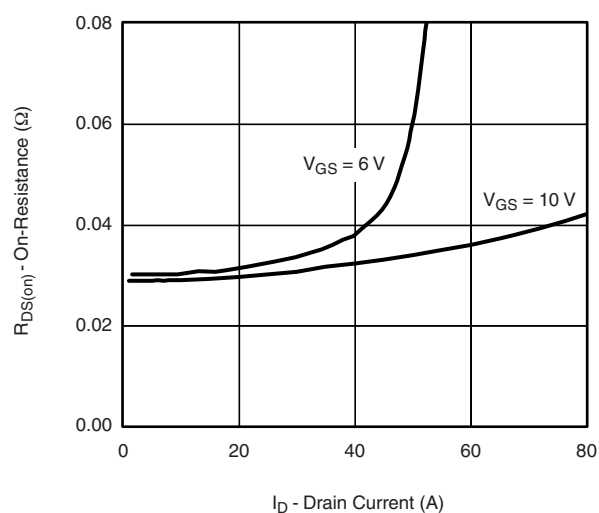
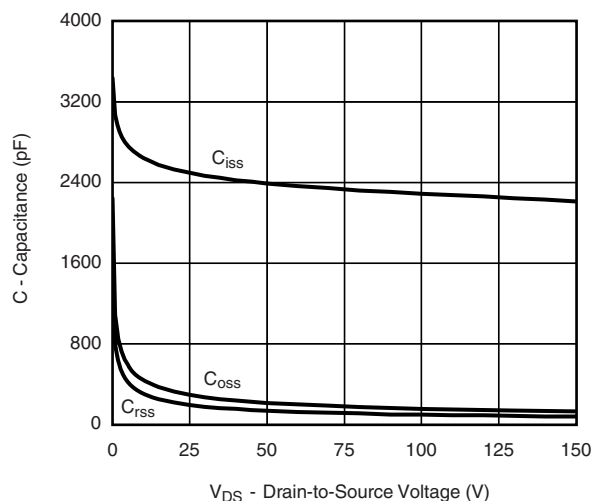
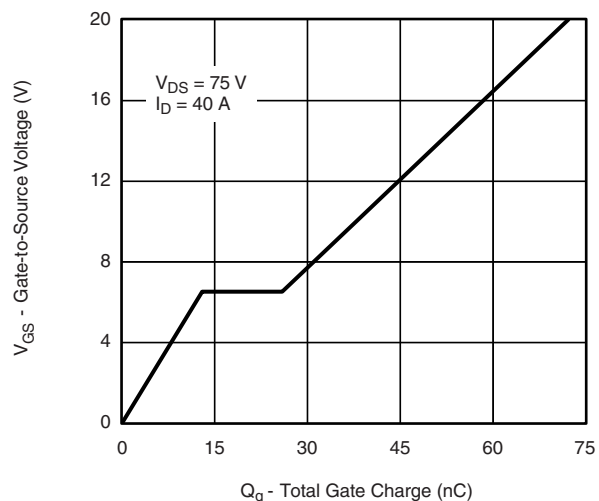
Notes:

a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ 

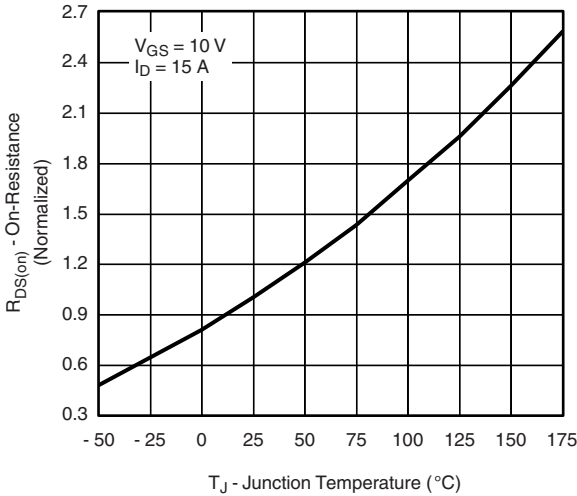
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

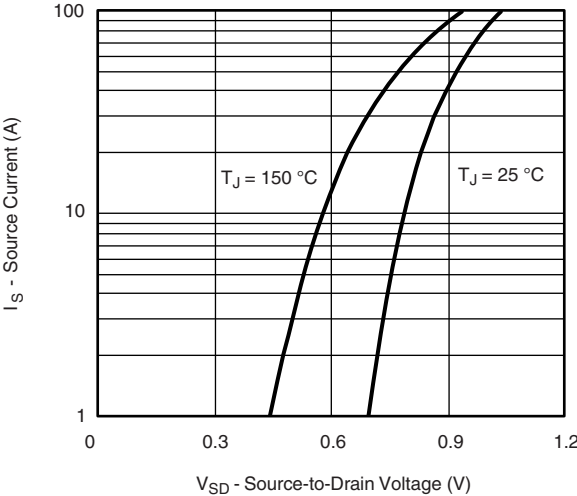
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

**Output Characteristics**

**Transfer Characteristics**

**Transconductance**

**On-Resistance vs. Drain Current**

**Capacitance**

**Gate Charge**

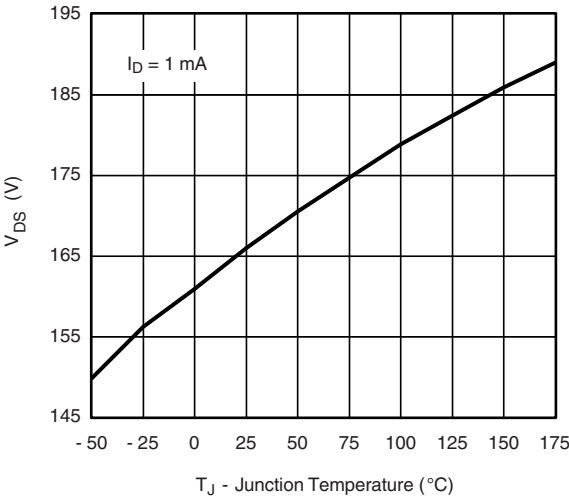
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**On-Resistance vs. Junction Temperature**



**Source-Drain Diode Forward Voltage**

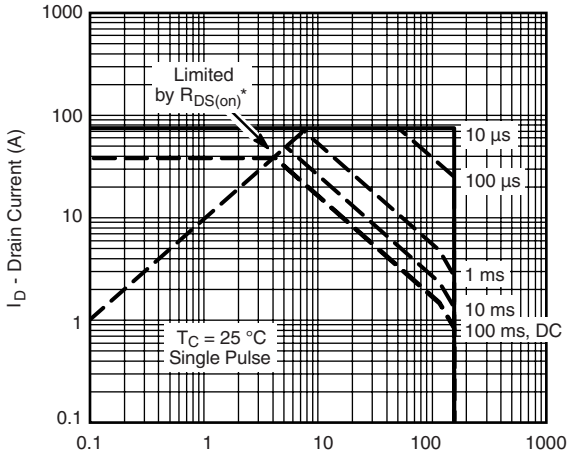


**Drain Source Breakdown vs. Junction Temperature**

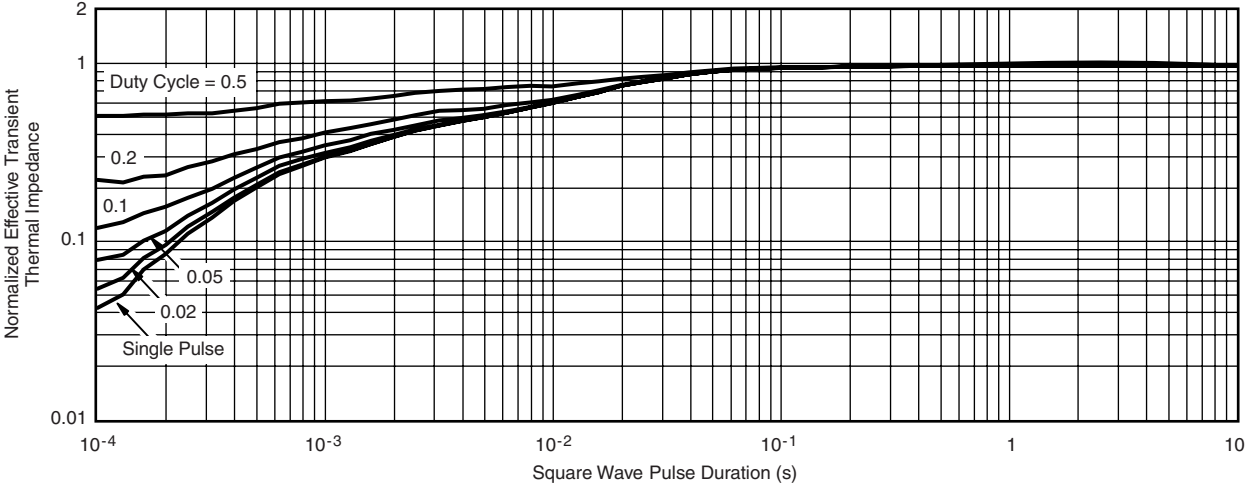
THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature

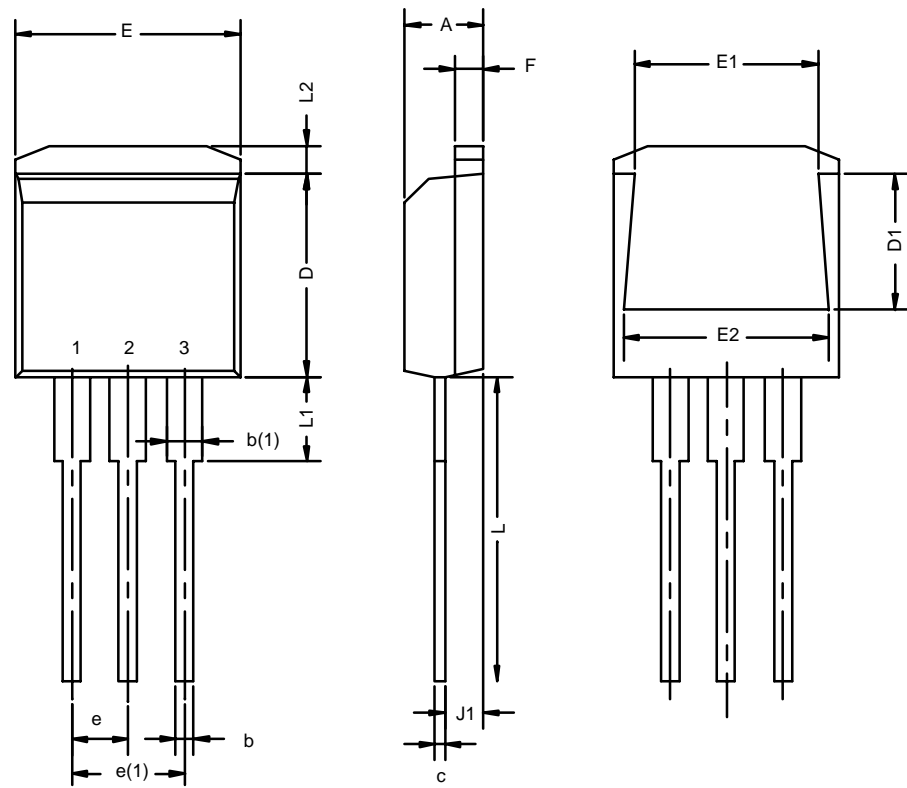


Safe Operating Area  
\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



Normalized Thermal Transient Impedance, Junction-to-Case

TO-262: 3-LEAD



Dim	MILLIMETERS*		INCHES	
	Min	Max	Min	Max
A	4.32	4.70	0.170	0.185
b	0.64	1.00	0.025	0.039
b(1)	1.14	1.40	0.045	0.055
c	0.36	0.50	0.014	0.020
D	8.64	9.65	0.340	0.380
D1	5.59	6.10	0.220	0.240
e	2.41	2.67	0.095	0.105
e(1)	4.95	5.33	0.195	0.210
E	10.03	10.41	0.395	0.410
E1	7.87	8.64	0.310	0.340
E2	9.02	9.53	0.355	0.375
F	1.14	1.40	0.045	0.055
J1	2.41	2.79	0.095	0.110
L	13.08	14.22	0.515	0.560
L1	-	3.81	-	0.150
L2	1.02	1.40	0.040	0.055
ECN: T-02234—Rev. C, 14-Oct-02				
DWG: 5855				

\*Use millimeters as the primary measurement

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